Appl No. 09/976,700 Amdt. dated August 28, 2003 Reply to Office Action of April 30, 2003

Amendments to the Specification:

Please amend Paragraph [0035] in the divisional application to delete Footnote 1 at the end

thereof:

[0035] To implement the bridge circuit 14 and the high voltage isolation capacitor 20 on the

same integrated circuit, certain characteristics are desirable for the components. Figures 4-8 show

cross-sections of preferred embodiments of these bridge circuit 14 components for use with the

invention. ¹

Please amend Paragraph [0037] in the divisional application to delete Footnote 1 at the end

thereof:

[0037] In addition to blocking reverse voltage, diode D1 26 must be fast enough to switch the

AC control signal from node N2. A problem which can arise with normal simple diodes P+/N- for

example, is that the injected forward current, holes in the N- material, is available only after the

minority carriers have recombined, resulting in a delay. This delay makes such devices relatively

slow. Faster switching is achieved if a bipolar connection is used. The minority carrier flow is only

through the base 40 and the current is readily available once it reaches the collector (N- substrate).

These devices are, therefore, much faster than the simple bipolar diodes. Proper polarity for the

diode is obtained when the substrate (P-)² is connected to the N-/well (and the P-base). Alternatively,

diode device D1 26 may be made using Schottky junction metal-semiconductors.

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